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Features

- Read Access Time 200 ns
- Automatic Page Write Operation
 - Internal Address and Data Latches for 256 Bytes
 - Internal Control Timer
- Fast Write Cycle Time
 - Page Write Cycle Time 10 ms Maximum
 - 1 to 256 Byte Page Write Operation
- Low Power Dissipation
 - 50 mA Active Current
- Hardware and Software Data Protection
- DATA Polling for End of Write Detection
- High Reliability CMOS Technology
 - Endurance: 10,000 Cycles
 - Data Retention: 10 Years
- Single 5V \pm 10% Supply
- CMOS and TTL Compatible Inputs and Outputs
- JEDEC Approved Byte-Wide Pinout

1. Description

The AT28C040 is a high-performance electrically erasable and programmable readonly memory (EEPROM). Its 4 megabits of memory is organized as 524,288 words by 8 bits. Manufactured with Atmel's advanced nonvolatile CMOS technology, the device offers access times to 200 ns with power dissipation of just 440 mW.

The AT28C040 is accessed like a static RAM for the read or write cycle without the need for external components. The device contains a 256-byte page register to allow writing of up to 256 bytes simultaneously. During a write cycle, the address and 1 to 256 bytes of data are internally latched, freeing the address and data bus for other operations. Following the initiation of a write cycle, the device will automatically write the latched data using an internal control timer. The end of a write cycle can be detected by Data Polling of I/O7. Once the end of a write cycle has been detected, a new access for a read or write can begin.

Atmel's AT28C040 has additional features to ensure high quality and manufacturability. The device utilizes internal error correction for extended endurance and improved data retention characteristics. An optional software data protection mechanism is available to guard against inadvertent writes. The device also includes an extra 256 bytes of EEPROM for device identification or tracking.



4-Megabit (512K x 8) Paged Parallel EEPROMs

AT28C040

0542F-PEEPR-2/09





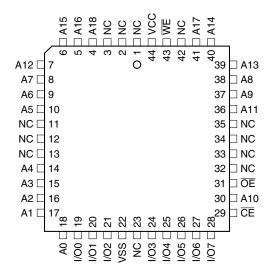
2. Pin Configurations

Pin Name	Function
A0 - A18	Addresses
CE	Chip Enable
ŌĒ	Output Enable
WE	Write Enable
I/O0 - I/O7	Data Inputs/Outputs
NC	No Connect

2.2 32-lead Flatpack – Top View

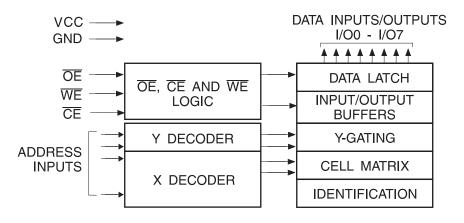
				1
A18 🗆	1	0	32	
A16 🗆	2		31	
A15 🗆	3		30	A17
A12 🗆	4		29	🗆 A14
A7 🗆	5		28	🗆 A13
A6 🗆	6		27	🗆 A8
A5 🗆	7		26	🗆 A9
A4 🗆	8		25	🗆 A11
A3 🗆	9		24	
A2 🗆	10		23	🗆 A10
A1 🗆	11		22	
A0 🗆	12		21	1/07
I/O0 □	13		20	1/06
I/O1 □	14		19	□ I/O5
I/O2 🗆	15		18	1/04
GND 🗆	16		17	□ I/O3

2.1 44-lead LCC – Top View



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3. Block Diagram



4. Absolute Maximum Ratings*

Temperature Under Bias55°C to +125°C
Storage Temperature65°C to +150°C
All Input Voltages (including NC pins) with Respect to Ground0.6V to +6.25V
All Output Voltages with Respect to Ground0.6V to V_{CC} + 0.6V
Voltage on $\overline{\text{OE}}$ and A9 with Respect to Ground0.6V to +13.5V

*NOTICE: Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.





5. Device Operation

5.1 Read

The AT28C040 is accessed like a static RAM. When \overline{CE} and \overline{OE} are low and \overline{WE} is high, the data stored at the memory location determined by the address pins is asserted on the outputs. The outputs are put in the high impedance state when either \overline{CE} or \overline{OE} is high. This dual-line control gives designers flexibility in preventing bus contention in their systems.

5.2 Byte Write

A low pulse on the $\overline{\text{WE}}$ or $\overline{\text{CE}}$ input with $\overline{\text{CE}}$ or $\overline{\text{WE}}$ low (respectively) and $\overline{\text{OE}}$ high initiates a write cycle. The address is latched on the falling edge of $\overline{\text{CE}}$ or $\overline{\text{WE}}$, whichever occurs last. The data is latched by the first rising edge of $\overline{\text{CE}}$ or $\overline{\text{WE}}$. Once a byte write has been started, it will automatically time itself to completion. Once a programming operation has been initiated and for the duration of t_{WC} , a read operation will effectively be a polling operation.

5.3 Page Write

The page write operation of the AT28C040 allows 1 to 256 bytes of data to be written into the device during a single internal programming period. A page write operation is initiated in the same manner as a byte write; the first byte written can then be followed by 1 to 255 additional bytes. Each successive byte must be written within 150 μ s (t_{BLC}) of the previous byte. If the t_{BLC} limit is exceeded, the AT28C040 will cease accepting data and commence the internal programming operation. All bytes during a page write operation must reside on the same page as defined by the state of the A8 - A18 inputs. For each WE high to low transition during the page write operation, A8 - A18 must be the same.

The A0 to A7 inputs specify which bytes within the page are to be written. The bytes may be loaded in any order and may be altered within the same load period. Only bytes which are specified for writing will be written; unnecessary cycling of other bytes within the page does not occur.

5.4 Data Polling

The AT28C040 features Data Polling to indicate the end of a write cycle. During a byte or page write cycle an attempted read of the last byte written will result in the complement of the written data to be presented on I/O7. Once the write cycle has been completed, true data is valid on all outputs, and the next write cycle may begin. Data Polling may begin at anytime during the write cycle.

5.5 Toggle Bit

In addition to Data Polling, the AT28C040 provides another method for determining the end of a write cycle. During the write operation, successive attempts to read data from the device will result in I/O6 toggling between one and zero. Once the write has completed, I/O6 will stop tog-gling and valid data will be read. Reading the toggle bit may begin at any time during the write cycle.

5.6 Data Protection

If precautions are not taken, inadvertent writes may occur during transitions of the host system power supply. Atmel[®] has incorporated both hardware and software features that will protect the memory against inadvertent writes.

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5.6.1 Hardware Protection

Hardware features protect against inadvertent writes to the AT28C040 in the following ways: (a) V_{CC} sense – if V_{CC} is below 3.8V (typical) the write function is inhibited; (b) V_{CC} power-on delay – once V_{CC} has reached 3.8V the device will automatically time out 5 ms (typical) before allowing a write: (c) write inhibit – holding any one of \overline{OE} low, \overline{OE} high or \overline{WE} high inhibits write cycles; (d) noise filter – pulses of less than 15 ns (typical) on the \overline{WE} or \overline{CE} inputs will not initiate a write cycle.

5.6.2 Software Data Protection

A software controlled data protection feature has been implemented on the AT28C040. When enabled, the software data protection (SDP), will prevent inadvertent writes. The SDP feature may be enabled or disabled by the user; the AT28C040 is shipped from Atmel with SDP disabled.

SDP is enabled when the host system issues a series of three write commands; three specific bytes of data are written to three specific addresses (refer to Software Data Protection Algorithm). After writing the 3-byte command sequence and after t_{WC} , the entire AT28C040 will be protected against inadvertent write operations. It should be noted that once protected, the host can still perform a byte or page write to the AT28C040. To do so, the same 3-byte command sequence used to enable SDP must precede the data to be written.

Once set, SDP will remain active unless the disable command sequence is issued. Power transitions do not disable SDP, and SDP will protect the AT28C040 during power-up and power-down conditions. All command sequences must conform to the page write timing specifications. The data in the enable and disable command sequences is not written to the device, and the memory addresses used in the sequence may be written with data in either a byte or page write operation.

After setting SDP, any attempt to write to the device without the 3-byte command sequence will start the internal write timers. No data will be written to the device; however, for the duration of t_{WC} , read operations will effectively be polling operations.

5.7 Device Identification

An extra 256 bytes of EEPROM memory are available to the user for device identification. By raising A9 to $12V \pm 0.5V$ and using address locations 7FF80H to 7FFFFH, the bytes may be written to or read from in the same manner as the regular memory array.

5.8 Optional Chip Erase Mode

The entire device can be erased using a 6-byte software erase code. Please see Software Chip Erase application note for details.





6. DC and AC Operating Range

		AT28C040-20 Operation	
		Read	Program
	Industrial	-40°C - 85°C	-40°C - 85°C
Operating Temperature (Case)	Extended	-55°C - 125°C	-40°C - 85°C
V _{CC} Power Supply		5V ± 10%	$5V\pm10\%$

7. Operating Modes

Mode	CE	ŌĒ	WE	I/O
Read	V _{IL}	V _{IL}	V _{IH}	D _{OUT}
Write ⁽²⁾	V _{IL}	V _{IH}	V _{IL}	D _{IN}
Write Inhibit	х	х	V _{IH}	
Write Inhibit	Х	V _{IL}	Х	
Output Disable	Х	V _{IH}	Х	High Z

Notes: 1. X can be V_{IL} or V_{IH} .

2. Refer to AC Programming Waveforms.

8. DC Characteristics

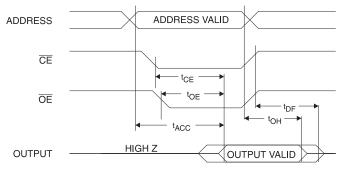
Symbol	Parameter	Condition	Min	Max	Units
ILI	Input Load Current	$V_{IN} = 0V$ to $V_{CC} + 1V$		10	μΑ
I _{LO}	Output Leakage Current	$V_{I/O} = 0V$ to V_{CC}		10	μA
I _{CC}	V _{CC} Active Current	$f = 5 \text{ MHz}; I_{OUT} = 0 \text{ mA}$		50	mA
V _{IL}	Input Low Voltage			0.8	V
V _{IH}	Input High Voltage		2.0		V
V _{OL}	Output Low Voltage	I _{OL} = 2.1 mA		0.45	V
V _{OH1}	Output High Voltage	I _{OH} = -400 μA	2.4		V
V _{OH2}	Output High Voltage CMOS	I _{OH} = -100 μA; V _{CC} = 4.5V	4.2		V

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9. AC Read Characteristics

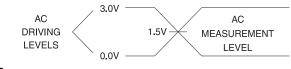
		AT28C		
Symbol	Parameter	Min	Max	Units
t _{ACC}	Address to Output Delay		200	ns
t _{CE} ⁽¹⁾	CE to Output Delay		200	ns
t _{OE} ⁽²⁾	OE to Output Delay	0	55	ns
t _{DF} ⁽³⁾⁽⁴⁾	CE or OE to Output Float	0	55	ns
t _{OH}	Output Hold from OE, CE or Address, whichever occurred first	0		ns

10. AC Read Waveforms⁽¹⁾⁽²⁾⁽³⁾⁽⁴⁾



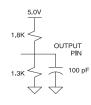
- Notes: 1. \overline{CE} May be delayed up to t_{ACC} t_{CE} after the address transition without impact on t_{ACC} .
 - OE may be delayed up to t_{CE} t_{OE} after the falling edge of CE without impact on t_{CE} or by t_{ACC} t_{OE} after an address change without impact on t_{ACC}.
 - 3. t_{DF} is specified from \overline{OE} or \overline{CE} , whichever occurs first (C_L = 5 pF).
 - 4. This parameter is characterized and is not 100% tested.

11. Input Test Waveforms and Measurement Level



t_R, t_F < 5 ns

12. Output Test Load



13. Pin Capacitance

 $f = 1 \text{ MHz}, T = 25^{\circ}C^{(1)}$

Symbol	Тур	Мах	Units	Conditions
C _{IN}	4	10	pF	$V_{IN} = 0V$
C _{OUT}	8	12	pF	$V_{OUT} = 0V$

Note: 1. This parameter is characterized and is not 100% tested.



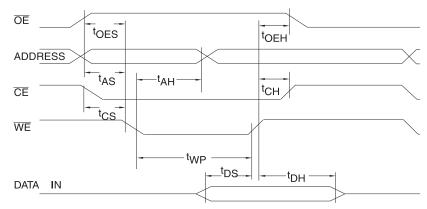


14. AC Write Characteristics

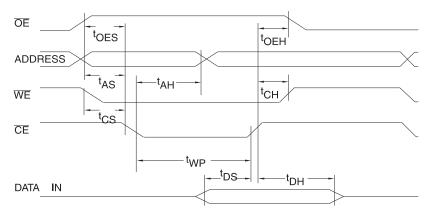
Symbol	Parameter	Min	Мах	Units
t _{AS} , t _{OES}	Address, OE Set-up Time	0		ns
t _{AH}	Address Hold Time	50		ns
t _{cs}	Chip Select Set-up Time	0		ns
t _{CH}	Chip Select Hold Time	0		ns
t _{WP}	Write Pulse Width (\overline{WE} or \overline{CE})	100		ns
t _{DS}	Data Set-up Time	50		ns
t _{DH} , t _{OEH}	Data, OE Hold Time	0		ns

15. AC Write Waveforms

15.1 WE Controlled



15.2 CE Controlled

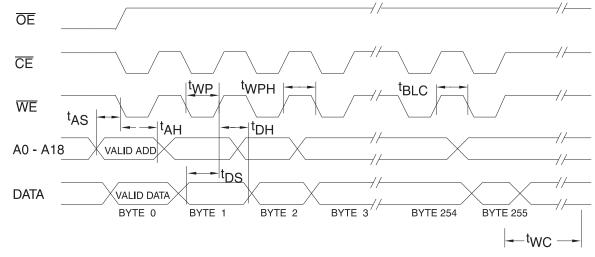


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16. Page Mode Characteristics

Symbol	Parameter	Min	Max	Units
t _{wc}	Write Cycle Time		10	ms
t _{AS}	Address Set-up Time	0		ns
t _{AH}	Address Hold Time	50		ns
t _{DS}	Data Set-up Time	50		ns
t _{DH}	Data Hold Time	0		ns
t _{WP}	Write Pulse Width	100		ns
t _{BLC}	Byte Load Cycle Time		150	μS
t _{WPH}	Write Pulse Width High	50		ns

17. Page Mode Write Waveforms⁽¹⁾⁽²⁾



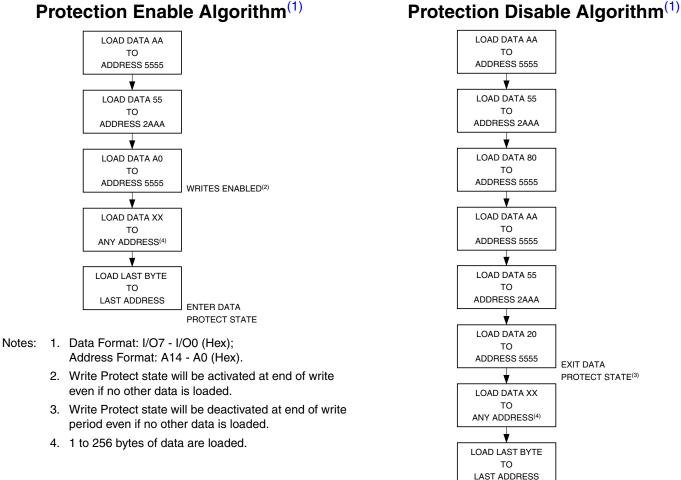
Notes: 1. A8 through A18 must specify the page address during each high to low transition of \overline{WE} (or \overline{CE}).

2. $\overline{\text{OE}}$ must be high only when $\overline{\text{WE}}$ and $\overline{\text{CE}}$ are both low.



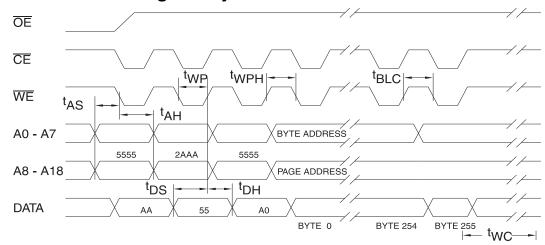


19. Software Data



18. Software Data Protection Enable Algorithm⁽¹⁾

20. Software Protected Program Cycle Waveform⁽¹⁾⁽²⁾⁽³⁾



- Notes: 1. A0 A14 must conform to the addressing sequence for the first 3 bytes as shown above.
 - 2. After the command sequence has been issued and a page write operation follows, the page address inputs (A8 A18) must be the same for each high to low transition of \overline{WE} (or \overline{CE}).
 - 3. OE must be high only when WE and CE are both low.

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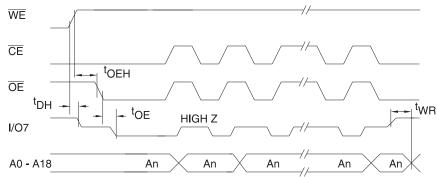
21. Data Polling Characteristics⁽¹⁾

Symbol	Parameter	Min	Тур	Max	Units
t _{DH}	Data Hold Time	10			ns
t _{OEH}	OE Hold Time	10			ns
t _{OE}	OE to Output Delay ⁽²⁾				ns
t _{wR}	Write Recovery Time	0			ns

Notes: 1. These parameters are characterized and not 100% tested.

2. See AC Read Characteristics.

22. Data Polling Waveforms



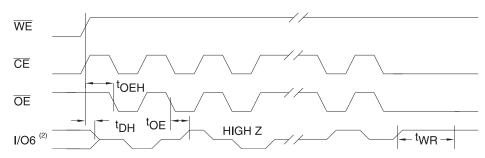
23. Toggle Bit Characteristics⁽¹⁾

Symbol	Parameter	Min	Тур	Max	Units
t _{DH}	Data Hold Time	10			ns
t _{OEH}	OE Hold Time	10			ns
t _{OE}	OE to Output Delay ⁽²⁾				ns
t _{OEHP}	OE High Pulse	150			ns
t _{WR}	Write Recovery Time	0			ns

Notes: 1. These parameters are characterized and not 100% tested.

2. See AC Read Characteristics.

24. Toggle Bit Waveforms⁽¹⁾⁽²⁾⁽³⁾



Notes: 1. Toggling either OE or CE or both OE and CE will operate toggle bit.

- 2. Beginning and ending state of I/O6 will vary.
- 3. Any address location may be used but the address should not vary.





25. Ordering Information

25.1 Standard Packaging

t _{ACC} (ns)	I _{CC} (mA)			
	Active	Ordering Code	Package	Operation Range
200	50	AT28C040-20FI	32F	Industrial
		AT28C040-20LI	44L	(-40° to 85°C)
	50	AT28C040-20FI SL703	32F	Extended
		AT28C040-20LI SL703	44L	(See DC and AC Operating Range Table)

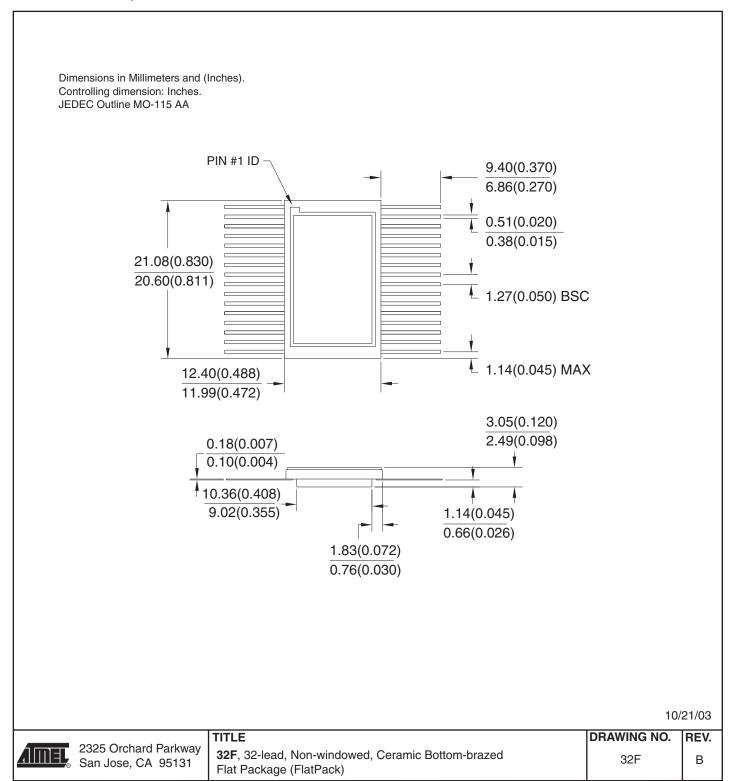
Note: 1. SL703 requires testing to Mil-883 standards; SL703 is marked on the package.

Package Type					
32F	32-Lead, Non-Windowed, Ceramic Bottom-Brazed Flat Package (Flatpack)				
44L	44-Pad, Non-Windowed, Ceramic Leadless Chip Carrier (LCC)				
	Options				
Blank	Blank Standard Device: Endurance = 10K Write Cycles; Write Time = 10 ms				

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26. Packaging Information

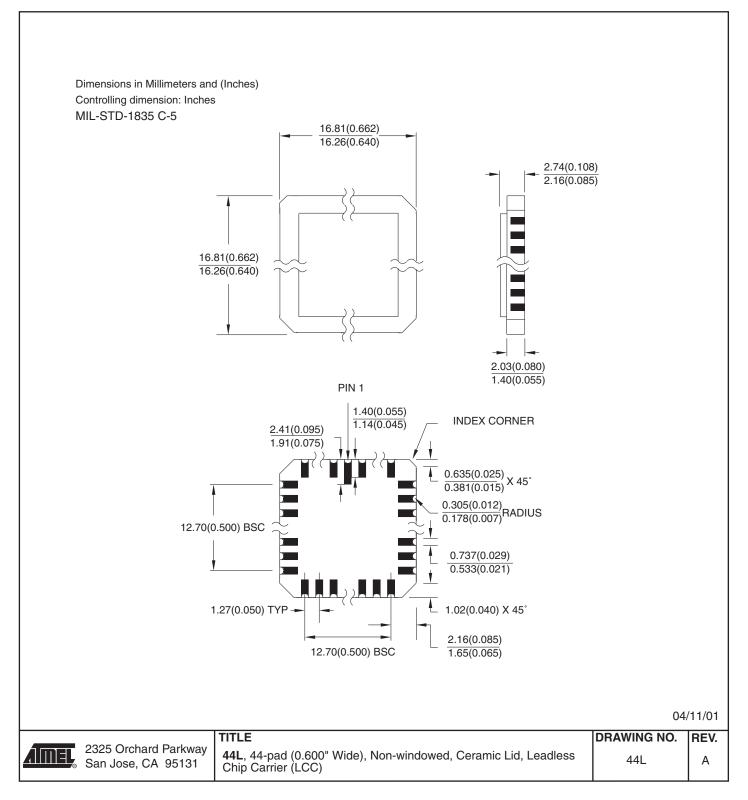
26.1 32F - Flatpack







26.2 44L - LCC





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